



晶体管 TRANSISTOR C2655A

主要参数 MAIN CHARACTERISTICS

I _c	2A
V _{CEO}	50V
P _c	0.9W

产品特性 FEATURES

硅外延	Epitaxial silicon
高开关速度	High switching speed
与 A1020 互补	Complementary to A1020
RoHS 产品	RoHS product

用途 APPLICATIONS

高频开关电源	High frequency switch power supply
一般功率放大电路	Commonly power amplifier circuit
高频功率变换	High frequency power transform

封装形式 Package



TO-92LS

绝对最大额定值 ABSOLUTE RATINGS (T_c=25°C)

项目 Parameter	符号 Symbol	数值 Value	单位 Unit
集电极—基极直流电压 Collector- Base Voltage (I _E =0)	V _{CB0}	50	V
集电极—发射极直流电压 Collector- Emitter Voltage (I _B =0)	V _{CEO}	50	V
发射极—基极直流电压 Emitter-Base Voltage (I _C =0)	V _{EB0}	5	V
最大集电极直流电流 Collector Current (DC)	I _c	2	A
最大集电极耗散功率 Total Dissipation (TO-92)	P _c	0.9	W
最高结温 Junction Temperature	T _j	150	°C
贮存温度 Storage Temperature	T _{stg}	-55~+150	°C

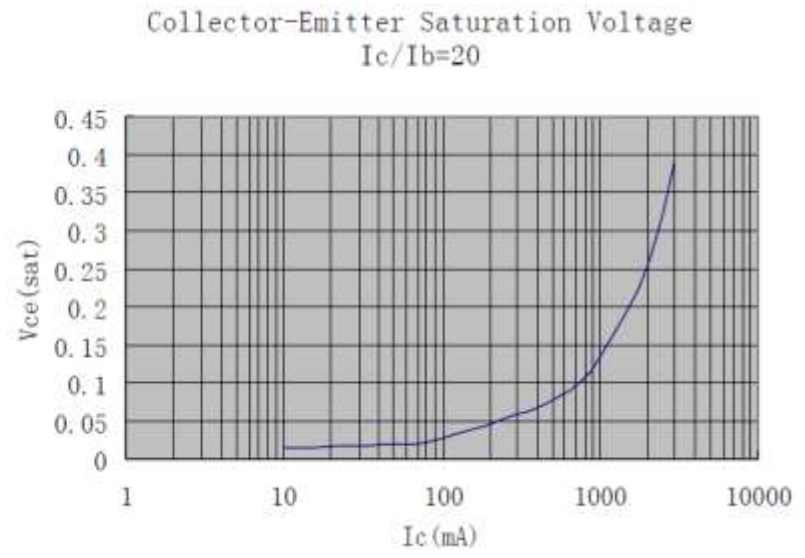
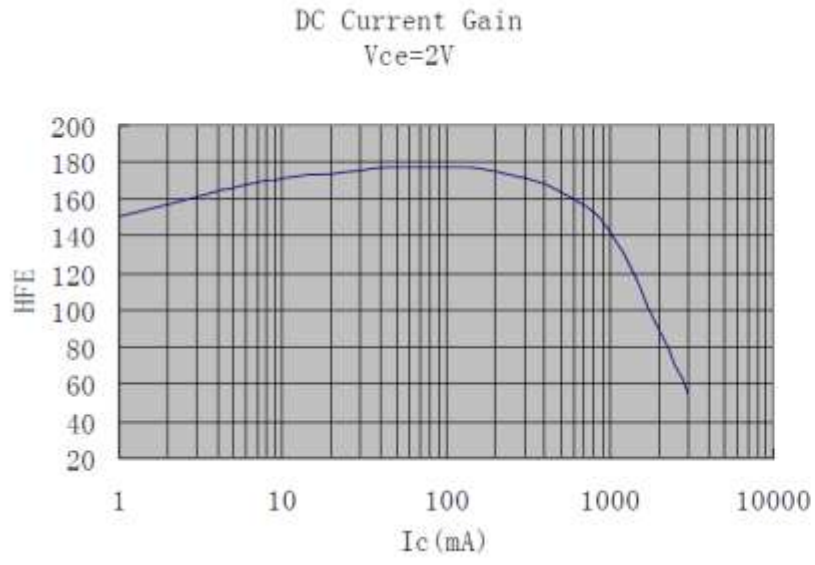
电特性 ELECTRICAL CHARACTERISTICS

项目 Parameter	测试条件 Tests conditions	最小值 (min)	典型值 (typ)	最大值 (max)	单位 Unit
V(BR) _{CBO}	I _C =100μA, I _E =0	50	-	-	V
V(BR) _{CEO}	I _C =10mA, I _B =0	50	-	-	V
V(BR) _{EBO}	I _E =100μA, I _C =0	5	-	-	V
I _{CBO}	V _{CB} =50V, I _E =0	-	-	1	μA
I _{EBO}	V _{EB} =5V, I _C =0	-	-	1	μA
HFE(1)	V _{CE} =2V, I _C =0.5A	70	-	400	
HFE(2)	V _{CE} =2V, I _C =1.5A	40	-	-	
V _{CE(sat)}	I _C =1.0A, I _B =0.05A	-	-	0.5	V
V _{BE(sat)}	I _C =1.0A, I _B =0.05A	-	-	1.2	V
f _T	V _{CE} =2V, I _C =0.5A	50	100	-	MHz

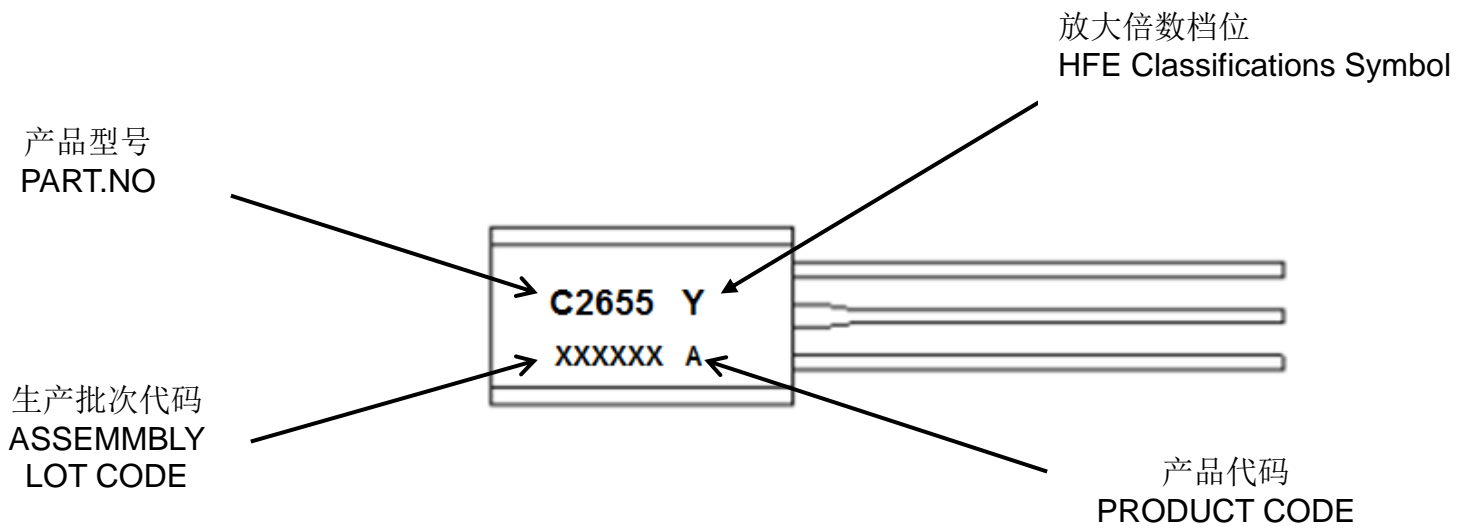
放大倍数 Hfe Classifications

HFE Classifications	O	Y	G
HFE Range	70-140	120-240	200-400

典型特效曲线 Electrical Characteristics

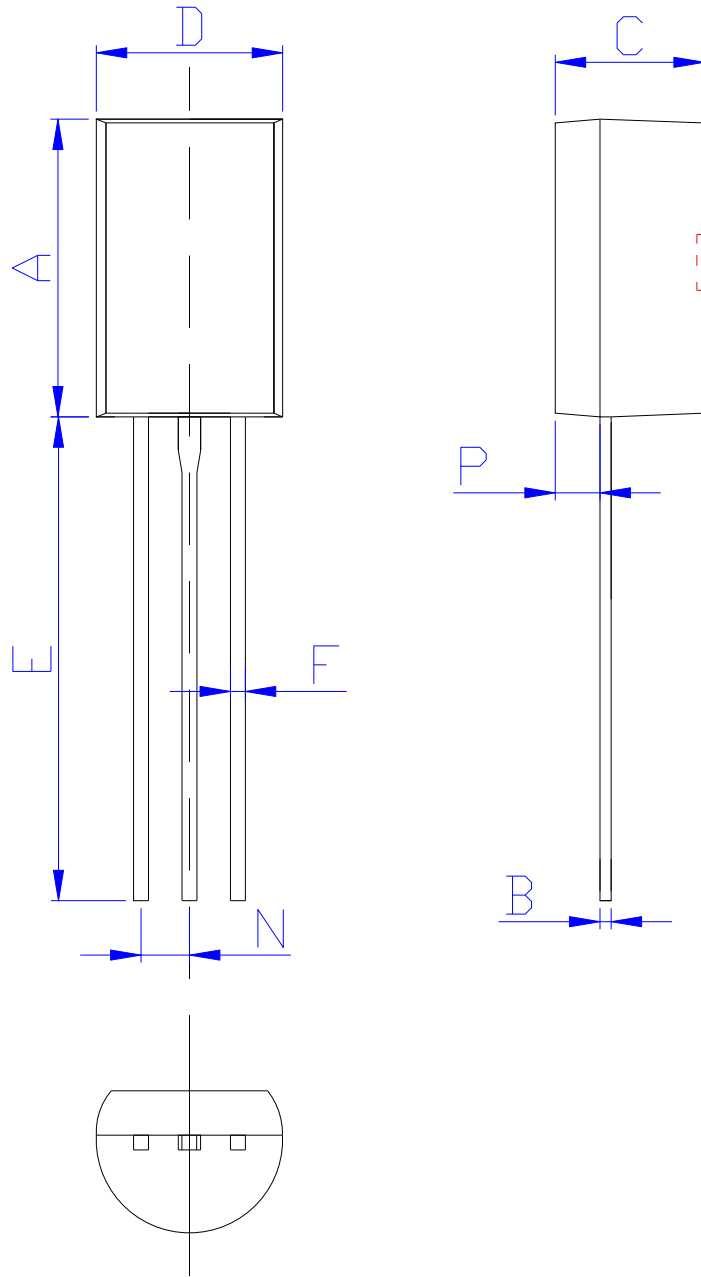


印记 Marking:



外形尺寸：
Package Dimension:

TO-92LS



DIM	MILLIMETERS
A	8.00 ± 0.30
B	0.40 ± 0.25
C	3.80 ± 0.30
D	4.90 ± 0.30
E	13.50 ± 0.30
F	0.50 ± 0.15
N	1.22 ± 0.25
P	1.40 ± 0.30

(Units: mm)